

IN THE CLAIMS

Please amend the claim as follows:

1. (Currently Amended) A method of growing a semiconductor layer in a selective area by MOCVD (Metal Organic Chemical Vapor Deposition), comprising the steps of:
 - (a) forming a first mask pattern on a semiconductor substrate having a (100) crystalline plane, ~~said first mask pattern having a first window wider than the selective area;~~
 - (b) forming a second mask pattern adjoining a first window and a window adjacent to the first mask pattern, wherein the first window represents the selective area, and wherein the window adjacent to the first mask pattern separates the second mask pattern from the first mask pattern and comprises having both a second window and a third window, the second and third windows being defined by spacing of the second mask pattern from the first mask pattern, in correspondence with corresponding to a blocking area for blocking the surface migration of a III-group semiconductor source gases at edges of the first third window, and the third window being as wide as the selective area; and
 - (c) growing the semiconductor layer having a trapezoidal shape by MOCVD on the semiconductor substrate exposed by the ~~second and third windows~~ first window and the window adjacent to the first mask pattern; and
 - (d) forming a trench by etching the semiconductor substrate exposed by the window adjacent to the first mask pattern.

2. (Original) The method of claim 1, wherein the first and second mask patterns and the first, second and third windows are formed in parallel to the (100) crystalline plane of the semiconductor substrate.

3. (Currently Amended) The method of claim 2, wherein step (b) includes forming the second mask pattern -such that at least one pair of the second windows are defined, window adjacent to the first mask pattern is configured to ~~for~~ forming at least one pair of blocking areas, and wherein the thickness of the semiconductor layer grown in the selective area is controlled by adjusting a number the semiconductor grown on the window adjacent to the first mask pattern or a width of the second windows window adjacent to the first mask pattern.

4. (Original) The method of claim 1, wherein the semiconductor layer grown in the selective area is an active layer for an SSC-LD (Spot-Size Converter integrated Laser Diode).

5. (Original) The method of claim 1, wherein the semiconductor layer grown in the selective area is formed of AlGaInAs.

6. (Canceled)

7. (Original) A method of growing a semiconductor layer in a selective area by MOCVD (Metal Organic Chemical Vapor Deposition), comprising the steps of:

(a) forming a first mask pattern; on a semiconductor substrate having a (100) crystalline plane, ~~said first mask pattern having a first window being wider than the selective area;~~

(b) forming a second mask pattern adjoining a first window and a window adjacent to the first mask pattern, wherein the first window represents the selective area, and wherein the window adjacent to the first mask pattern separates the second mask pattern from the first mask pattern and comprises ~~having at least one second window and a third window, the second and~~

~~third windows being defined by spacing the second mask pattern from the first mask pattern, in correspondence with to a blocking area for blocking the surface migration of -III-group semiconductor source gases at edges of the first third window, and the third window being as wide as the selective area;~~

- (c) forming at least one trench by etching the semiconductor substrate exposed by the ~~second window~~ window adjacent to the first mask pattern; and
- (d) growing the semiconductor layer by MOCVD on the semiconductor substrate exposed by the ~~third-first~~ window and the trench.

8. (Original) The method of claim 7, wherein both the first and second mask patterns and the first, second and third windows are formed in parallel to the (100) crystalline plane of the semiconductor substrate.

9. (Original) The method of claim 7, wherein the thickness of the semiconductor layer grown in the selective area is controlled by adjusting a number, width or depth of trenches.

10. (Original) The method of claim 7, wherein the trench is formed into the shape of a reverse mesa or a square.

11-17 (Canceled)